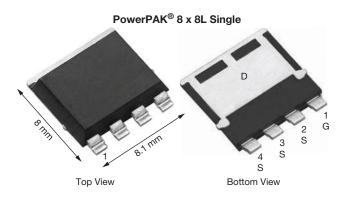
### SQJQ410EL



**Vishay Siliconix** 

# Automotive N-Channel 100 V (D-S) 175 °C MOSFET

PRODUCT SUMMARY						
V <sub>DS</sub> (V)	100					
$R_{DS(on)} (\Omega)$ at $V_{GS} = 10 V$	0.0034					
$R_{DS(on)} (\Omega)$ at $V_{GS} = 4.5 V$	0.0040					
I <sub>D</sub> (A)	135					
Configuration	Single					
Package	PowerPAK 8 x 8L					

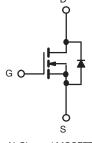


#### FEATURES

- TrenchFET<sup>®</sup> power MOSFET
- AEC-Q101 qualified
- 100 % R<sub>q</sub> and UIS tested
- Fully lead (Pb)-free device
- Thin 1.9 mm height
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>



FREE



N-Channel MOSFET

ABSOLUTE MAXIMUM RATING	<b>S</b> (T <sub>C</sub> = 25 °C, unless	otherwise noted	)	
PARAMETER		SYMBOL	LIMIT	UNIT
Drain-Source Voltage		V <sub>DS</sub>	100	V
Gate-Source Voltage		V <sub>GS</sub>	± 20	v
Continuous Drain Current	T <sub>C</sub> = 25 °C	1-	135	
Continuous Drain Current	T <sub>C</sub> = 125 °C	Ι <sub>D</sub>	78	
Continuous Source Current (Diode Conduct	ion)	I <sub>S</sub>	124	А
Pulsed Drain Current <sup>a</sup>		I <sub>DM</sub>	210	
Single Pulse Avalanche Current	L = 0.1 mH	I <sub>AS</sub>	68	
Single Pulse Avalanche Energy	L = 0.1 IIIA	E <sub>AS</sub>	231	mJ
Maximum Power Dissipation	T <sub>C</sub> = 25 °C	Р	136	W
Maximum Fower Dissipation	Im Power Dissipation $T_{C} = 125 \text{ °C}$ $P_{D}$ 45		VV	
Operating Junction and Storage Temperature Range		T <sub>J</sub> , T <sub>stg</sub>	-55 to +175	°C
Soldering Recommendations (Peak Temperature) c, d			260	U

THERMAL RESISTANCE RATINGS				
PARAMETER		SYMBOL	LIMIT	UNIT
Junction-to-Ambient	PCB Mount <sup>b</sup>	R <sub>thJA</sub>	50	°C/W
Junction-to-Case (Drain)		R <sub>thJC</sub>	1.1	0/10

#### Notes

a. Pulse test; pulse width  $\leq$  300 µs, duty cycle  $\leq$  2 %.

b. When mounted on 1" square PCB (FR4 material).

c. See solder profile (<u>www.vishay.com/doc?73257</u>). The PowerPAK 8 x 8L is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection.

d. Rework conditions: manual soldering with a soldering iron is not recommended for leadless components.

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SQJQ410EL

SPECIFICATIONS ( $T_C = 25 \circ C$	, unless othe	erwise noted)						
PARAMETER	SYMBOL	TES	T CONDITIONS	MIN.	TYP.	MAX.	UNIT	
Static		•			•			
Drain-Source Breakdown Voltage	V <sub>DS</sub>	$V_{GS} = 0, I_D = 250 \ \mu A$		100	-	-	v	
Gate-Source Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =	= V <sub>GS</sub> , I <sub>D</sub> = 250 μΑ	1.5	2	2.5		
Gate-Source Leakage	I <sub>GSS</sub>	V <sub>DS</sub> =	$= 0 \text{ V}, \text{ V}_{\text{GS}} = \pm 20 \text{ V}$	-	-	± 100	nA	
		$V_{GS} = 0 V$	V <sub>DS</sub> = 100 V	-	-	1		
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	$V_{GS} = 0 V$	V <sub>DS</sub> = 100 V, T <sub>J</sub> = 125 °C	-	-	50	μA	
		$V_{GS} = 0 V$	V <sub>DS</sub> = 100 V, T <sub>J</sub> = 175 °C	-	-	500		
On-State Drain Current <sup>a</sup>	I <sub>D(on)</sub>	$V_{GS} = 10 V$	$V_{DS} \ge 5 V$	50	-	-	А	
		$V_{GS} = 10 V$	I <sub>D</sub> = 20 A	-	0.0028	0.0034		
Drain-Source On-State Resistance <sup>a</sup>	Р	$V_{GS} = 4.5 V$	I <sub>D</sub> = 10 A	-	0.0033	0.0040	Ω	
Drain-Source On-State Resistance	R <sub>DS(on)</sub>	$V_{GS} = 10 V$	I <sub>D</sub> = 20 A, T <sub>J</sub> = 125 °C	-	-	0.0058		
		$V_{GS} = 10 V$	I <sub>D</sub> = 20 A, T <sub>J</sub> = 175 °C	-	-	0.0074		
Forward Transconductance <sup>b</sup>	9 <sub>fs</sub>	V <sub>DS</sub> = 15 V, I <sub>D</sub> = 15 A		-	84	-	S	
Dynamic <sup>b</sup>								
Input Capacitance	Ciss			-	5620	7350		
Output Capacitance	C <sub>oss</sub>	$V_{GS} = 0 V$	V <sub>DS</sub> = 25 V, f = 1 MHz	-	2850	3750	рF	
Reverse Transfer Capacitance	C <sub>rss</sub>			-	220	290	1	
Total Gate Charge <sup>c</sup>	Qg			-	97	150		
Gate-Source Charge <sup>c</sup>	Q <sub>gs</sub>	$V_{GS} = 10 V$	$V_{DS} = 50 \text{ V}, \text{ I}_{D} = 10 \text{ A}$	-	15	-	nC	
Gate-Drain Charge <sup>c</sup>	Q <sub>gd</sub>			-	20	-	1	
Gate Resistance	Rg		f = 1 MHz		1.92	3	Ω	
Turn-On Delay Time <sup>c</sup>	t <sub>d(on)</sub>			-	19	30		
Rise Time <sup>c</sup>	t <sub>r</sub>	$V_{DD} = 50 \text{ V}, \text{ R}_{\text{I}} = 5 \Omega$		-	40	60	ns	
Turn-Off Delay Time <sup>c</sup>	t <sub>d(off)</sub>	I <sub>D</sub> ≅ 10 Å,	-	69	110			
Fall Time <sup>c</sup>	t <sub>f</sub>	1		-	87	135	1	
Source-Drain Diode Ratings and Cha	racteristics <sup>b</sup>							
Pulsed Current <sup>a</sup>	I <sub>SM</sub>			-	-	210	А	
Forward Voltage	V <sub>SD</sub>	I <sub>F</sub> =	= 40 A, V <sub>GS</sub> = 0 V	-	0.83	1.2	V	

Notes

a. Pulse test; pulse width  $\leq$  300 µs, duty cycle  $\leq$  2 %.

b. Guaranteed by design, not subject to production testing.

www.vishay.com

c. Independent of operating temperature.

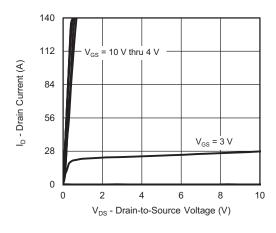
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



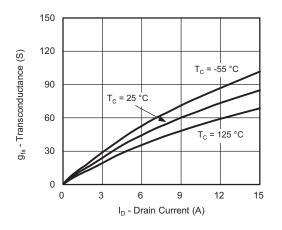
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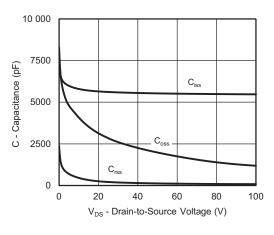
#### **TYPICAL CHARACTERISTICS** (T<sub>A</sub> = 25 °C, unless otherwise noted)



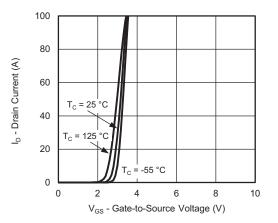
**Output Characteristics** 



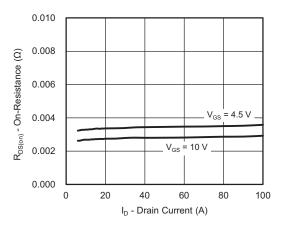
Transconductance



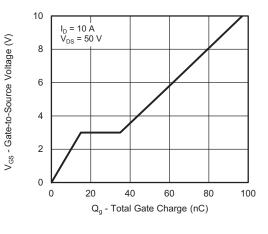
#### Capacitance



**Transfer Characteristics** 



**On-Resistance vs. Drain Current** 



Gate Charge

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3 s. contact: automostec Document Number: 76643

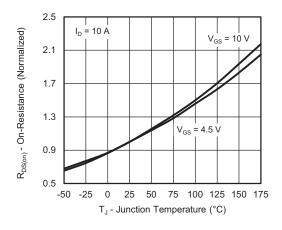
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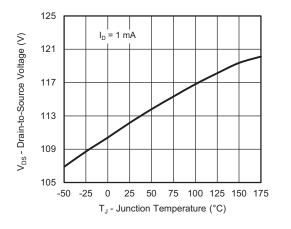
# SQJQ410EL

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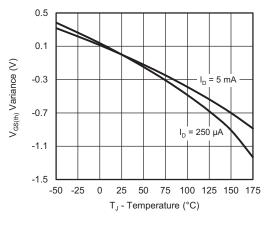
#### TYPICAL CHARACTERISTICS (T<sub>A</sub> = 25 °C, unless otherwise noted)



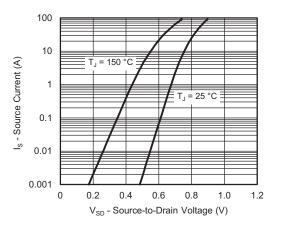
**On-Resistance vs. Junction Temperature** 



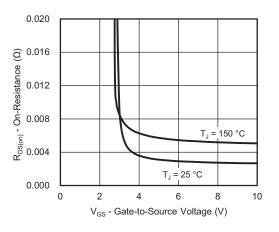
Drain Source Breakdown vs. Junction Temperature



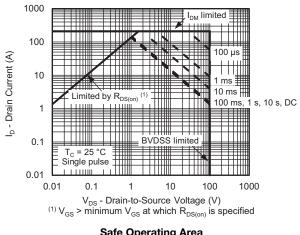
**Threshold Voltage** 



Source Drain Diode Forward Voltage



**On-Resistance vs. Gate-to-Source Voltage** 



Safe Operating Area

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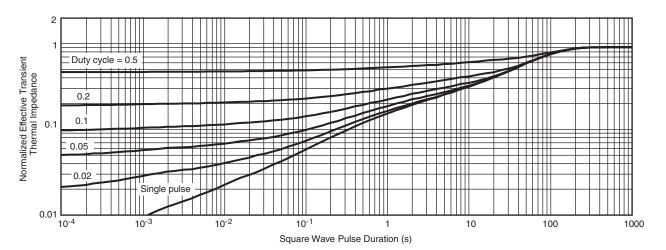
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Document Number: 76643

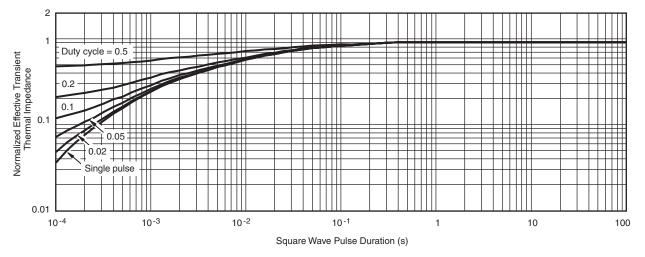
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#### THERMAL RATINGS (T<sub>A</sub> = 25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Ambient



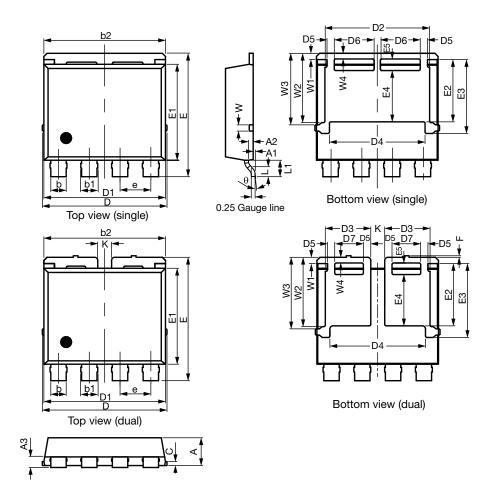
Normalized Thermal Transient Impedance, Junction-to-Case

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DIM.		MILLIMETERS		INCHES		
DIM.	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.
А	1.70	1.80	1.90	0.067	0.071	0.075
A1	0.00	0.08	0.13	0.000	0.003	0.005
A2	0.25	0.30	0.35	0.010	0.012	0.014
A3	0.55	0.62	0.70	0.022	0.024	0.028
b	0.92	1.00	1.08	0.036	0.039	0.043
b1	1.02	1.10	1.18	0.040	0.043	0.046
b2	7.80	7.90	8.00	0.307	0.311	0.315
С	0.20	0.25	0.30	0.008	0.010	0.012
D	8.00	8.10	8.25	0.315	0.319	0.325
D1	7.80	7.90	8.00	0.307	0.311	0.315
D2	6.70	6.80	6.90	0.264	0.268	0.272
D3	2.85	2.95	3.05	0.112	0.116	0.120
D4	6.11	6.21	6.31	0.241	0.244	0.248
D5	0.37	0.47	0.57	0.015	0.019	0.022
D6	2.49	2.59	2.69	0.098	0.102	0.106
D7	1.76	1.86	1.96	0.069	0.073	0.077

Revision: 16-Oct-17

Document Number: 67734

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# **Package Information**



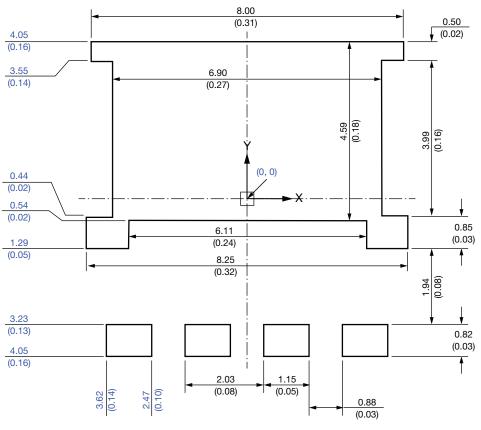


### Vishay Siliconix

DIM.		MILLIMETERS		INCHES			
	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.	
е	1.95	2.00	2.05	0.077	0.079	0.081	
Е	7.90	8.00	8.10	0.311	0.315	0.319	
E1	6.12	6.22	6.32	0.241	0.245	0.249	
E2	3.94	4.04	4.14	0.140	0.159	0.163	
E3	4.69	4.79	4.89	0.185	0.189	0.193	
E4	3.23	3.33	3.43	0.127	0.131	0.135	
E5	0.65	0.75	0.85	0.026	0.030	0.033	
F	0.00	0.10	0.15	0.000	0.004	0.006	
L	0.62	0.72	0.82	0.024	0.028	0.032	
L1	0.92	1.07	1.22	0.036	0.042	0.048	
К	0.80	0.90	1.00	0.031	0.035	0.039	
W	0.30	0.40	0.50	0.012	0.016	0.020	
W1	0.30	0.40	0.50	0.012	0.016	0.020	
W2	4.39	4.49	4.59	0.173	0.177	0.181	
W3	4.54	4.64	4.74	0.179	0.183	0.187	
W4	0.32	0.37	0.42	0.013	0.015	0.017	
θ	6°	10°	14°	6°	10°	14°	



# **Recommended Minimum PADs for PowerPAK® 8 x 8L Single**



Dimensions in millimeters (inches)

#### Note

• Linear dimensions are in black, the same information is provided in ordinate dimensions which are in blue.



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